

In the Claims

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Claim 1 (previously presented): A method of forming a monolayer of functionalized silicon on a substrate surface, the functionalized silicon including an organic group covalently attached with the silicon, the method comprising exposing the substrate surface to a precursor comprising the functionalized silicon under a pressure of at least 30 psi, the precursor interacting with the substrate to form the monolayer across at least a portion of the surface of the substrate; and wherein the exposing of the substrate surface to the precursor occurs in a supercritical fluid.

Claim 2 (canceled).

Claim 3 (original): The method of claim 1 wherein the pressure is at least 100 psi.

Claim 4 (original): The method of claim 1 wherein the pressure is at least 1000 psi.

Claim 5 (original): The method of claim 1 wherein the pressure is at least 4000 psi.

Claim 6 (original): The method of claim 1 wherein the pressure is at least 8000 psi.

Claim 7 (original): The method of claim 1 wherein the substrate comprises glass.

Claim 8 (currently amended): ~~A method of forming a fiberglass matrix, comprising:~~
~~providing a glass fiber having a surface;~~
~~providing a precursor containing functionalized silicon, the functionalized silicon~~
~~including an organic group covalently attached with the silicon;~~
~~exposing the glass fiber surface to the precursor under a pressure of at least 30 psi,~~
~~the precursor interacting with the surface to form a monolayer containing the functionalized~~
~~silicon across at least a portion of the surface; and~~

The method of claim 1 wherein the substrate comprises a glass fiber; and further
comprising, after forming the monolayer, incorporating the glass fiber into a fiberglass
matrix by bonding the organic group within a polymeric material.

Claim 9 (original): The method of claim 1 wherein the substrate comprises
aluminum, and the substrate surface comprises oxygen of aluminum oxide.

Claim 10 (original): The method of claim 1 wherein the substrate comprises a
silicon wafer, and the surface comprises oxygen of silicon dioxide.

Claim 11 (original): The method of claim 1 wherein the substrate surface
predominately comprises carbon.

Claim 12 (original): The method of claim 1 wherein the substrate surface comprises
silicon carbide.

Claim 13 (original): The method of claim 1 wherein the substrate comprises titanium, and the substrate surface comprises oxygen of titanium oxide.

Claim 14 (original): The method of claim 1 further comprising forming a film of water across a surface of the substrate prior to the exposing of the substrate to the precursor.

Claim 15 (original): The method of claim 1 wherein the precursor is selected from the group consisting of siloxanes, silazanes and chlorosilanes.

Claim 16 (previously presented): The method of claim 1 wherein the exposing of the substrate surface to the precursor occurs for a time of at least about 10 seconds.

Claim 17 (previously presented): The method of claim 1 wherein the exposing of the substrate surface to the precursor occurs for a time of at least about 30 seconds.

Claim 18 (previously presented): The method of claim 1 wherein the exposing of the substrate surface to the precursor occurs for a time of at least about minute.

Claims 19-29 (canceled).

Claim 30 (previously presented): A method of functionalizing an oxygen-containing

surface

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